

Polarized Photoguns and Prospects for Higher Current

More specifically:

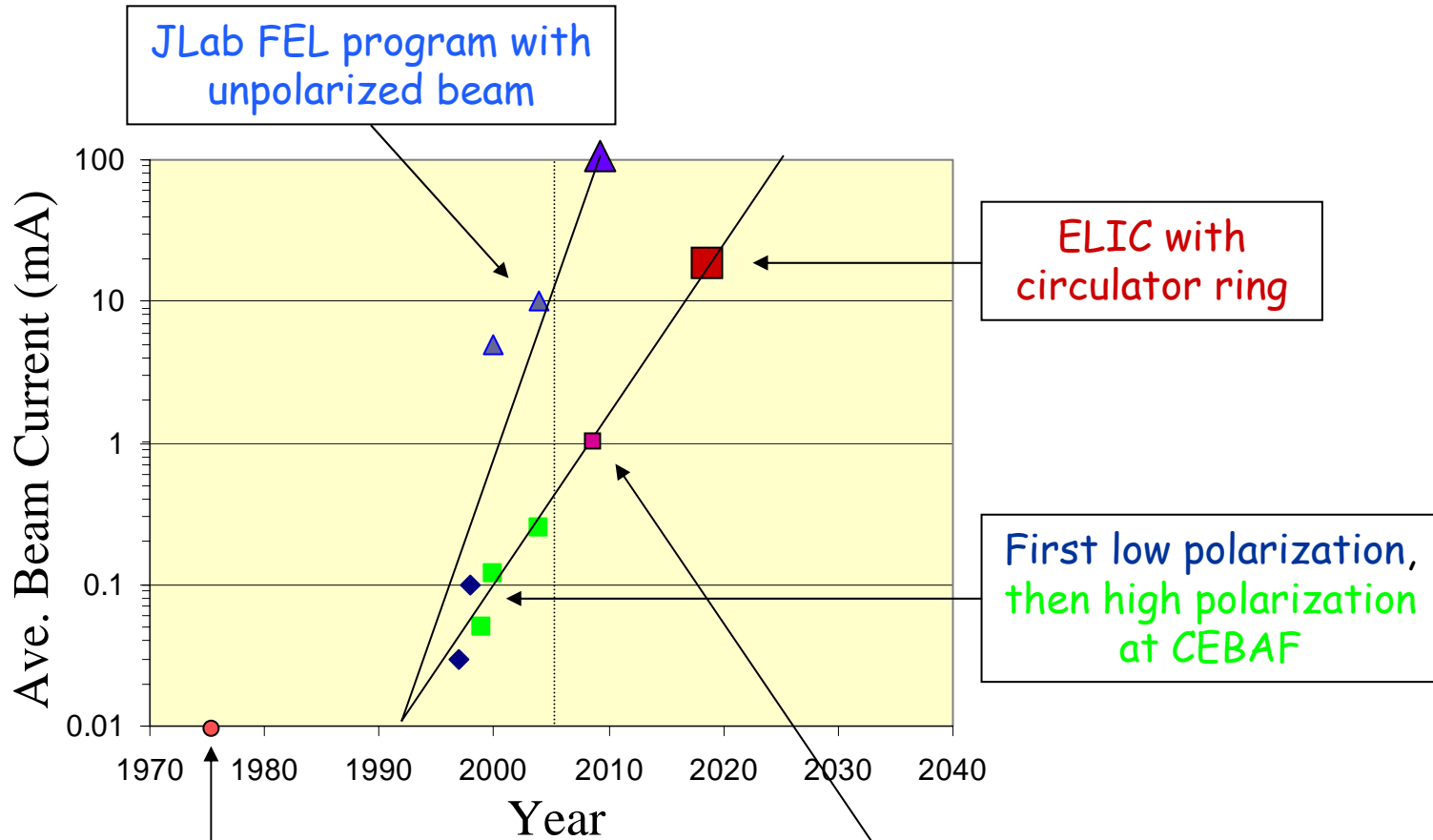
What will it take to provide
1 mA at 85% polarization?

M. Poelker
Jefferson Lab

ERL Workshop
Jefferson Lab
March 19 -22, 2005



Plot from EIC Workshop, Jefferson Lab, March 2004

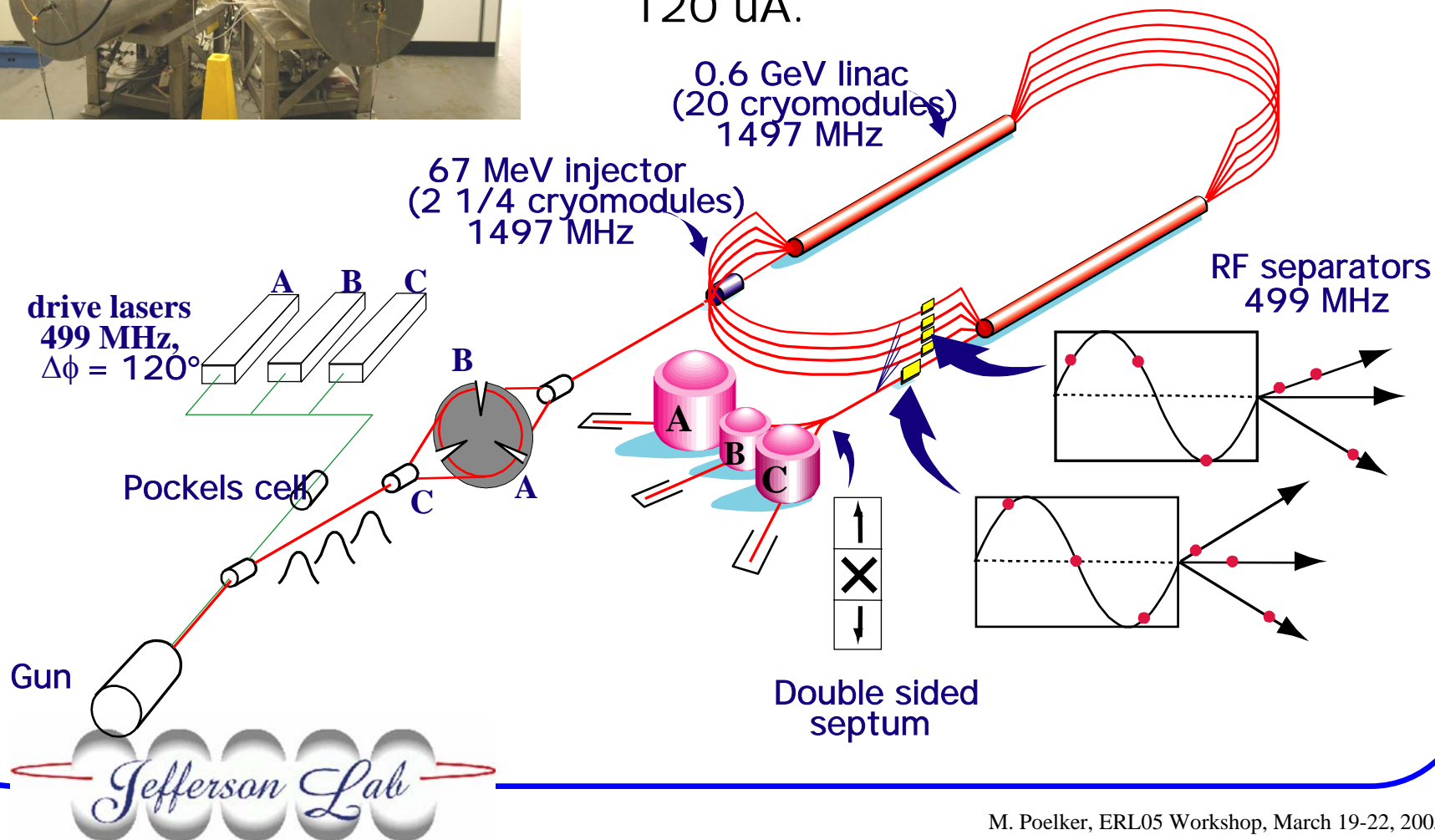


Today's talk to focus on modest extrapolation to 1 mA at 85% polarization



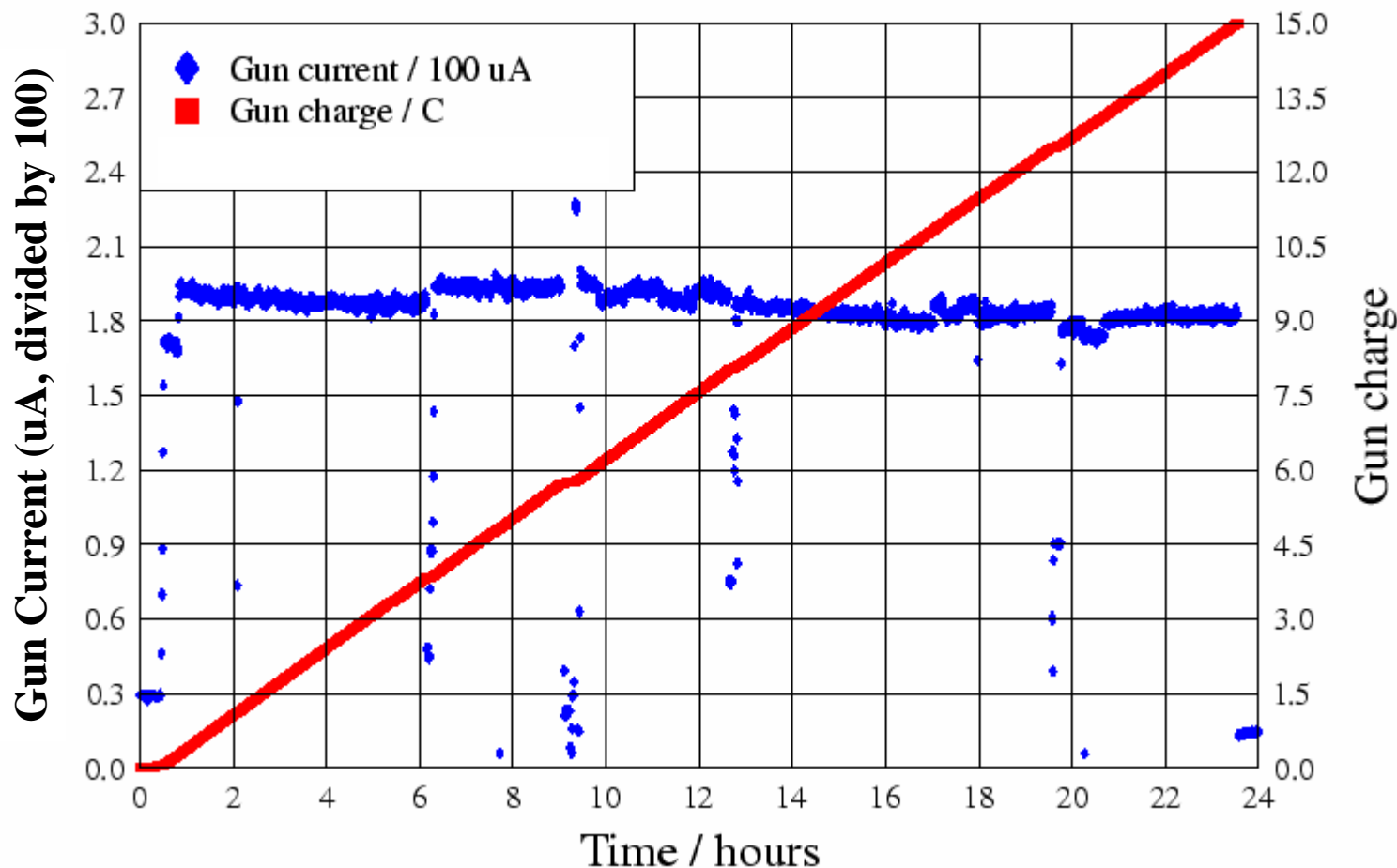


- Only DC high voltage GaAs photoguns are used at CEBAF
- All beam originates from ~ 0.5 mm spot on cathode
- Halls A and C can take up to 120 μ A.



A Good Day at CEBAF...

Uninterrupted beam with ~ 200 μA extracted from gun.
(Mostly, we operate near 100 μA)



What will it take to deliver 1 mA at high polarization?

This represents an improvement of state-of-the-art by factor of 5 to 10.

- **Good photocathode material**
 - Two commercial vendors
- **High power modelocked Ti-Sapphire lasers with GHz repetition rate**
 - One commercial vendor for rep rates to 500 MHz
 - One homemade system that needs work
- **Good gun lifetime**
 - Good static vacuum
 - Maintain good vacuum while delivering beam
- **Reliable hardware: lasers, gun and diagnostics.**



Commercial Photocathode Material

Strained GaAs from Bandwidth Semiconductor (Hudson, NH)

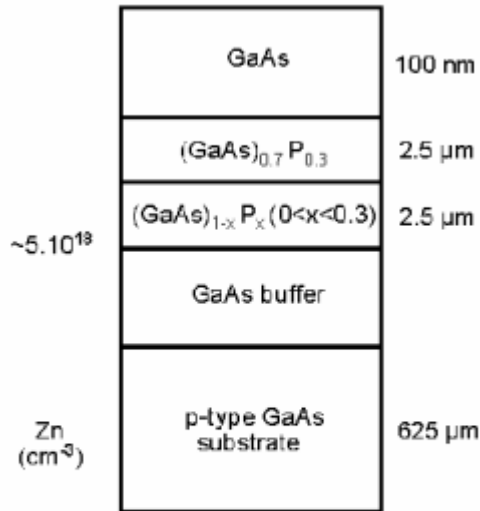
- Polarization ~ 75% with 0.15% QE at 855 nm
- Very reliable vendor, used for many years at CEBAF
- Large 3" diameter wafers, MOCVD, \$4.5K/each
- Easily anodized, easily cleaned with atomic hydrogen.
- Mild charge limit behavior when photocathode is "old".
- Large QE anisotropy (or analyzing power), ~ 12%

Strained Superlattice GaAs from SVT Associates (Eden Prairie, MN)

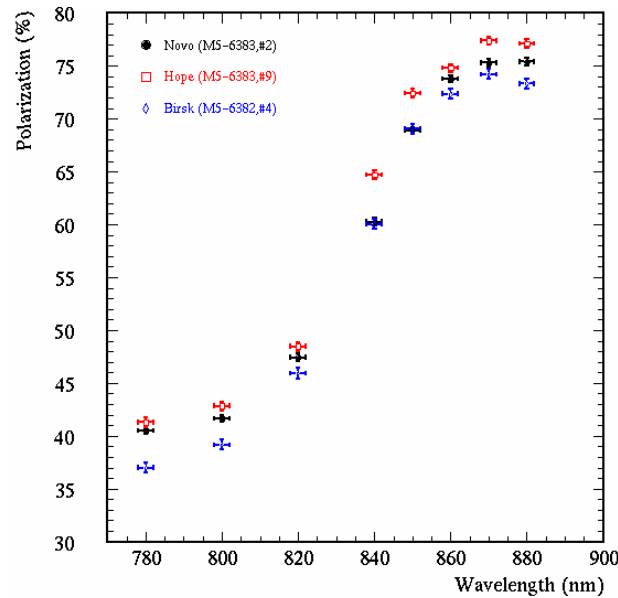
- Polarization ~85% and typical initial QE 1% at 780 nm
- Established vendor, new to photocathode business.
- 2" diameter wafers, MBE, \$6.3K/each
- Arsenic capped
- Tough to anodize because samples cannot be hydrogen cleaned
- Experience to date: pronounced charge limit problems.
- Small QE anisotropy, ~ 3%.

Items in red = "bad"

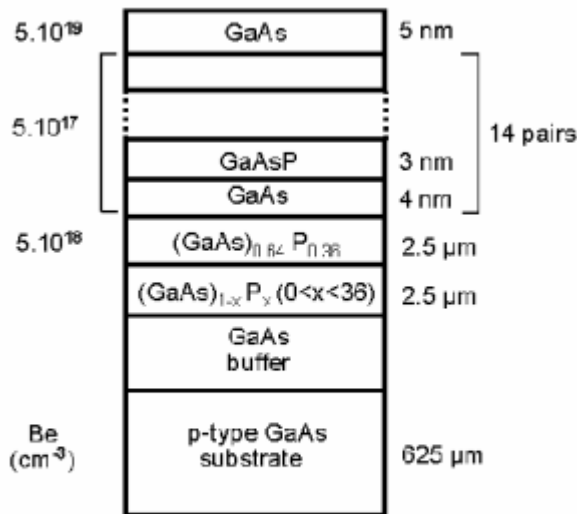




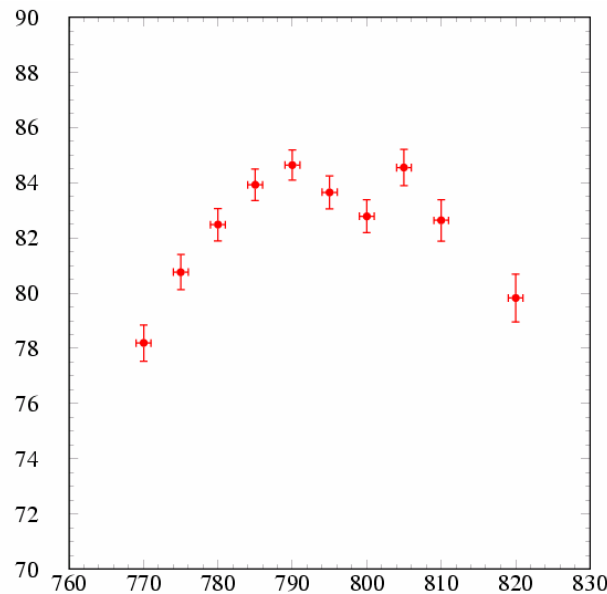
Strained-layer GaAs



Strained GaAs
 From Bandwidth Semiconductor
 Pol $\sim 75\%$
 QE $\sim 0.15\%$



Strained-superlattice GaAs



Strained Superlattice GaAs
 from SVT Assoc.
 Pol $\sim 85\%$
 QE $\sim 1\%$

Data from M. Baylac

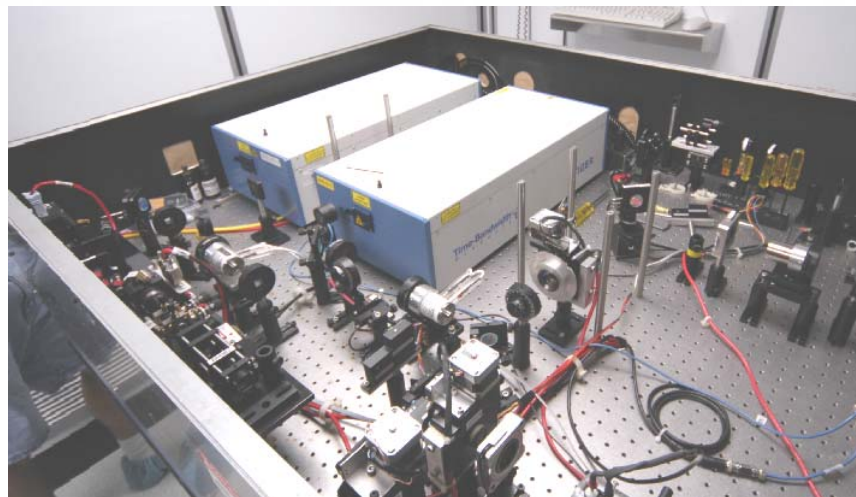
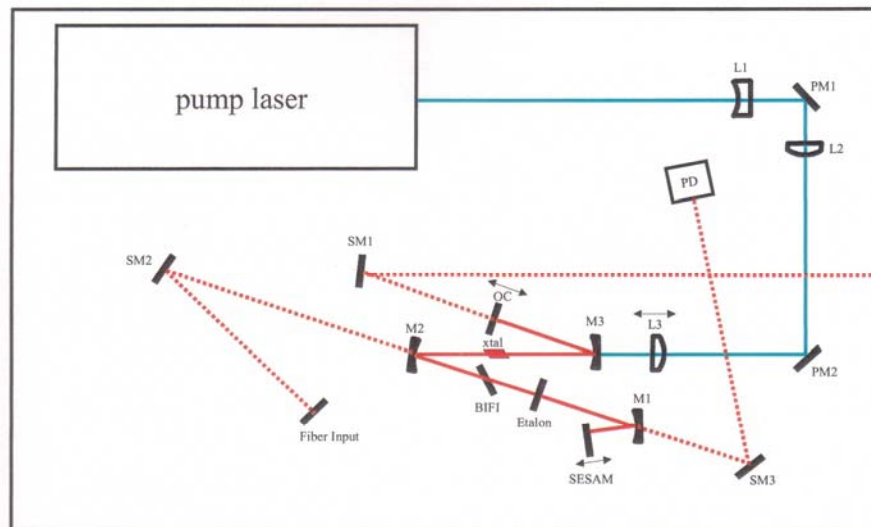
Modelocked Ti-Sapphire Lasers from TimeBandwidth

SESAM: passive modelocking for high rep rates



Time-Bandwidth®
P r o d u c t s

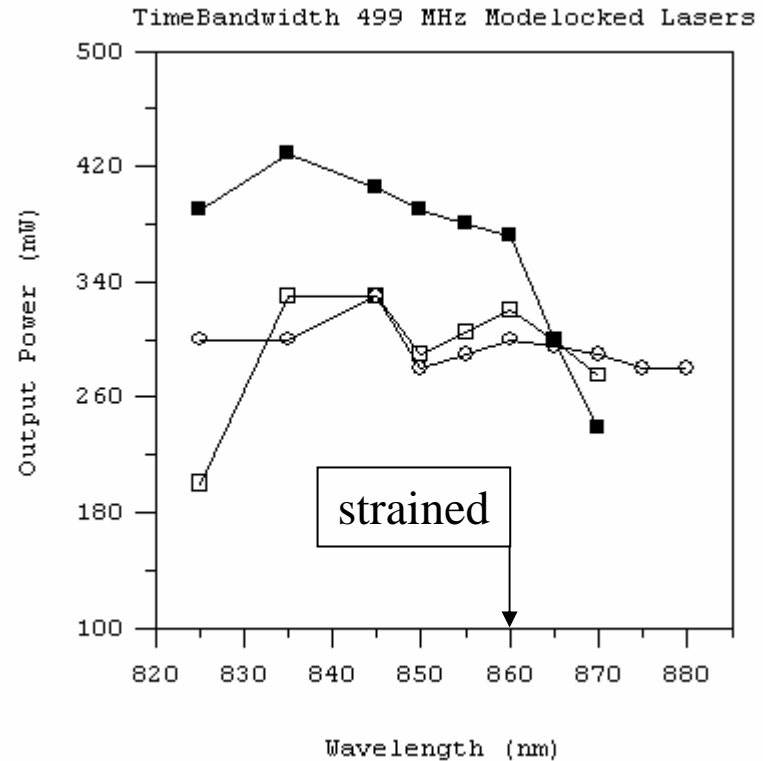
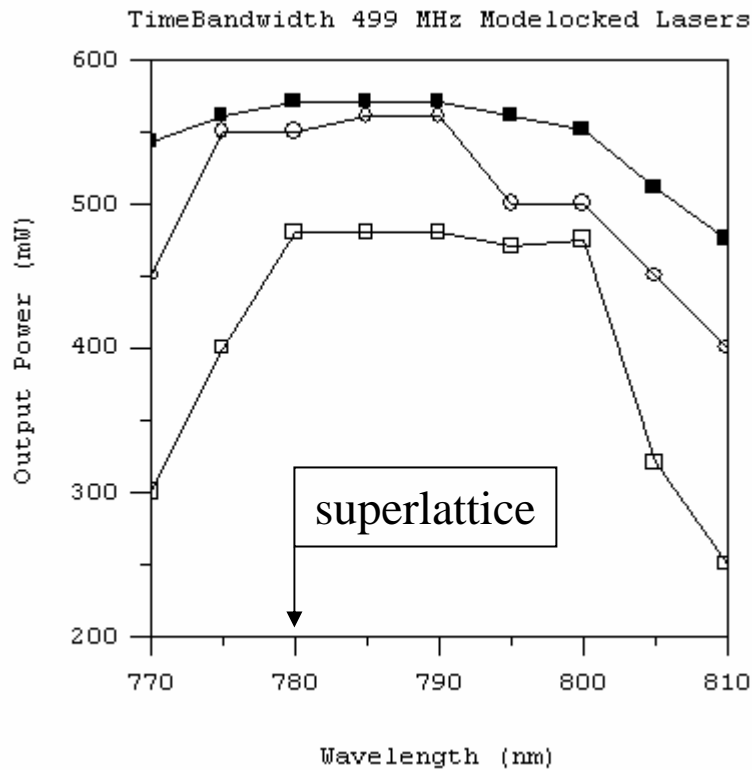
Technoparkstrasse 1, CH-8005 Zürich, Switzerland
Phone: ++41 1/445-3120 FAX: ++41 1/445-3121
Internet: info@tbwp.com www.tbwp.com



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- **Passive modelocking for high rep rates: CEBAF model = 499 MHz**
- **Selectable wavelength ranges near 770 nm or 850 nm**
- **Phase-locked pulse train is stable for days, weeks, months however...**
- **“laser jock” required.**
- **We also purchased a 31 MHz model with ~ 5 m cavity length.**



Maximum Beam Current with Existing Commercial Photocathodes and Lasers

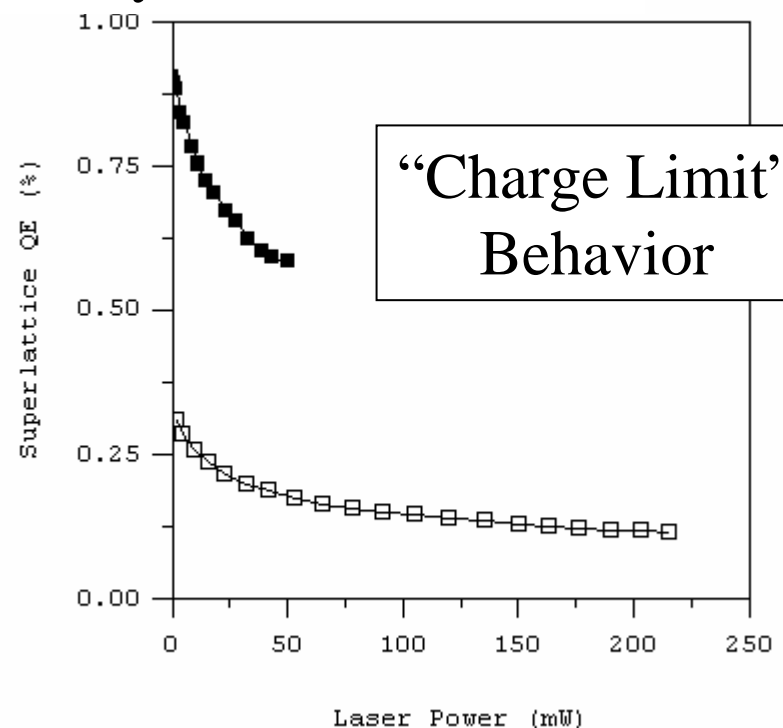
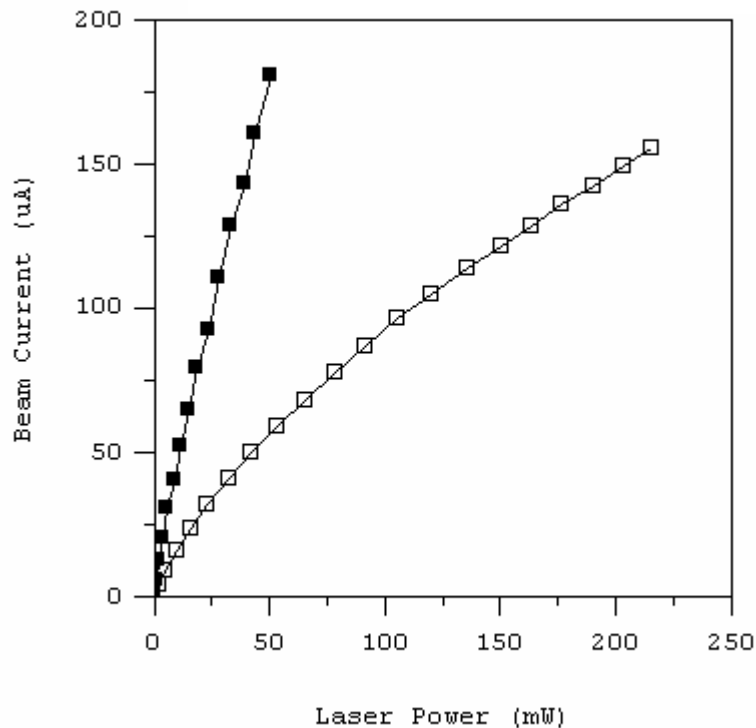
Photocathode Material	Polarization	Max. Initial QE	Max. Laser Power	Max. Current
Strained GaAs	75%	0.15%	300 mW at 860 nm	283 μ A
Strained Superlattice GaAs	85%	1%	500 mW at 780 nm	3145 μ A

Hooray!
(But not demonstrated)



Problems with Superlattice Photocathodes

After 1 month of beam delivery and 3rd activation very



- Photocathode QE not constant with increasing laser power
- Observed Lifetime not so good: 20 C instead of 200 C
- Problems Anodizing and Hydrogen Cleaning: we've had to change CEBAF procedure (tantalum mask, more later)



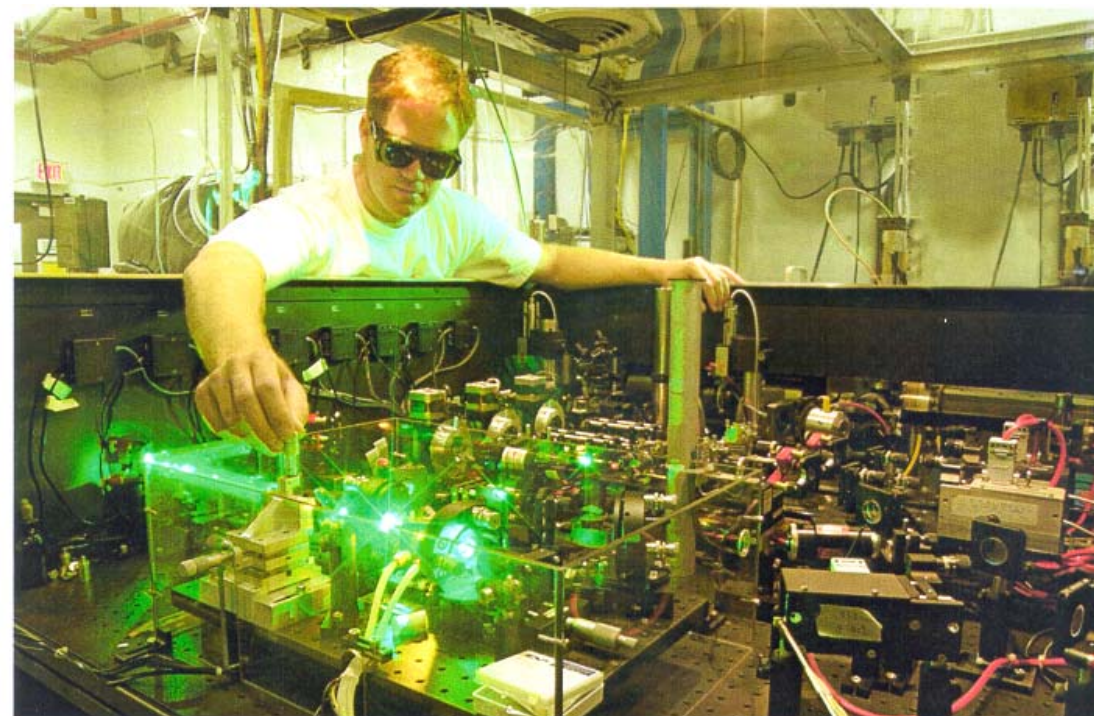
Revise Table to Account for Charge Limit

Photocathode Material	Polarization	Max. Initial QE	Max. Laser Power	Max. Current
Strained GaAs	75%	0.15%	300 mW at 860 nm	283 uA
Strained Superlattice GaAs - With charge limit	85%	0.15 %	500 mW at 780 nm	472 uA

Boo!

And I have not taken into account laser table optical losses.
Time to revisit JLab modelocked Ti-Sapphire laser...

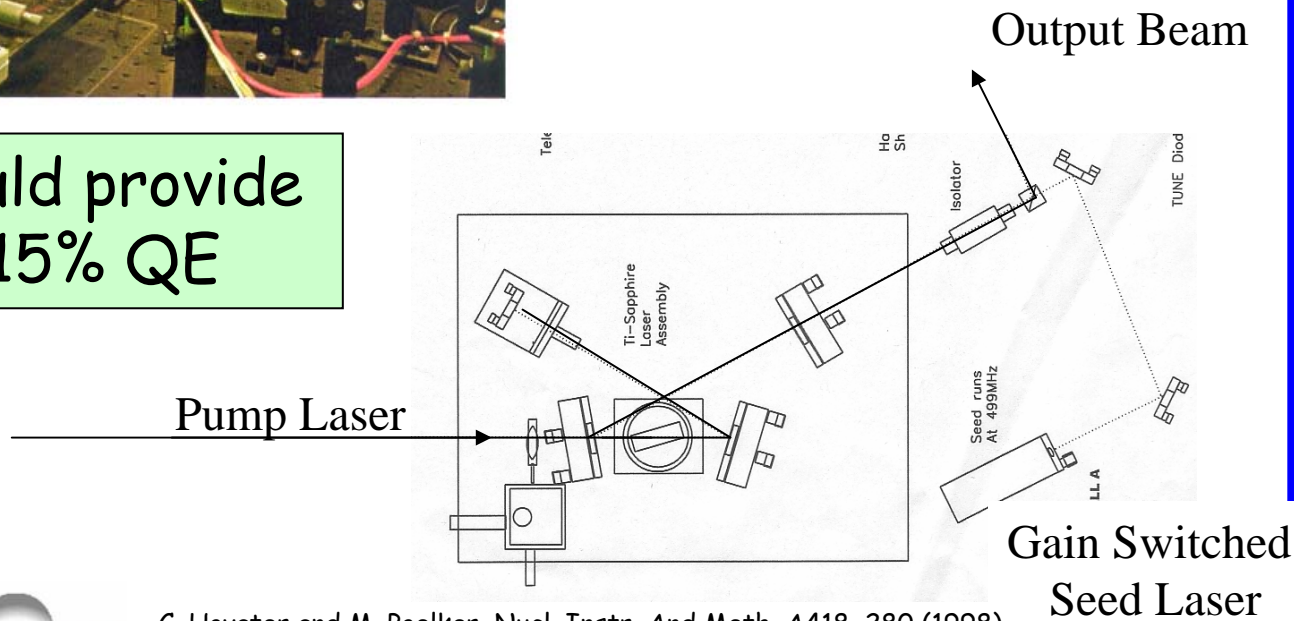




Harmonic Modelocked Ti-Sapphire Laser:

- Rep Rates to 3 GHz
- Used at CEBAF, 400 mW
- Lab version produced 2W
- Needs active stabilization

2 Watts would provide
1.8 mA at 0.15% QE



C. Hovater and M. Poelker, Nucl. Instr. And Meth. A418, 280 (1998).



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What Effects Gun Lifetime?

Ion backbombardment is the mechanism that causes QE degradation (where residual gas is ionized by extracted electron beam - ions are then back-accelerated toward photocathode)

Obtaining and **Maintaining** good vacuum inside gun is critical

- Baseline vacuum inside CEBAF guns 1×10^{-11} Torr
 - NEG + ion pumps
- Maintain good vacuum when extracting beam:
 - There are "good" electrons and "bad" electrons:
 - Deliver the good electrons and eliminate the bad electrons (or at least ensure they hit the vacuum chamber walls far from the gun).

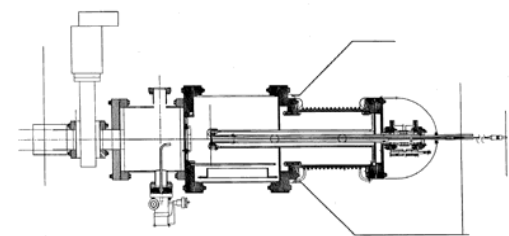
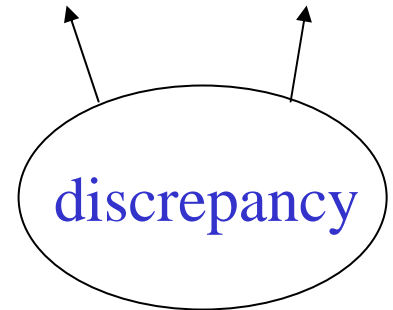
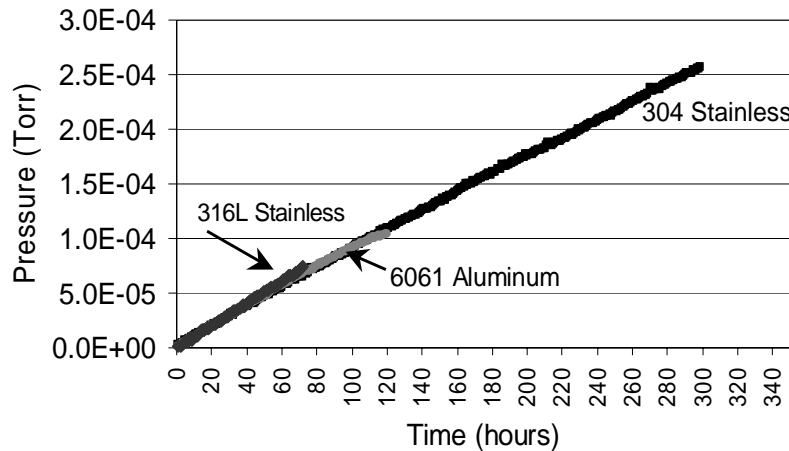


More on Gun Vacuum

$$\text{Ultimate Pressure} = \frac{\text{Outgassing Rate} \times \text{Surface Area}}{\text{Pump Speed}}$$

	Surface Area (sq cm)	Vacuum Pump	Ultimate Pressure (Torr)	Calculated Pumping Speed (l/s)	Installed Pumping Speed (l/s)
CEBAF Gun	6000	IP & NEG	1.0×10^{-11}	600	~6500

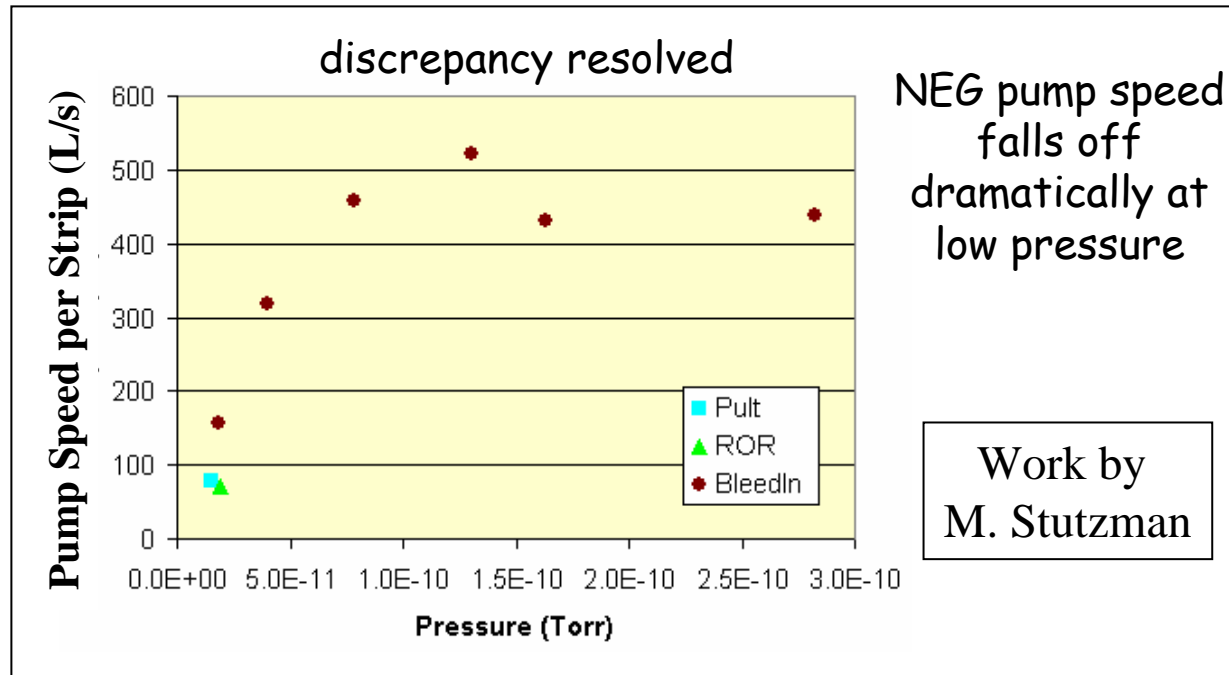
Outgassing Rate $\sim 1 \times 10^{-12}$ Torr L/sec cm²



"A Comparison of Outgassing Measurements For Three Vacuum Chamber Materials", P. Adderley, M. Stutzman, AVS Conf Proceedings, 2002.

How to Improve Gun Vacuum?

Preliminary measurements



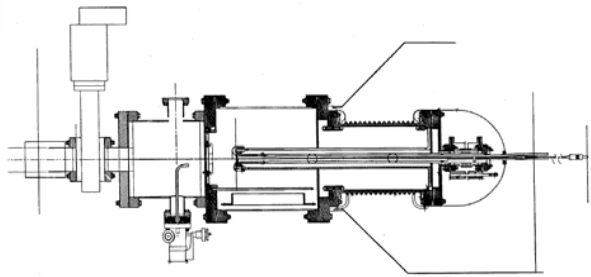
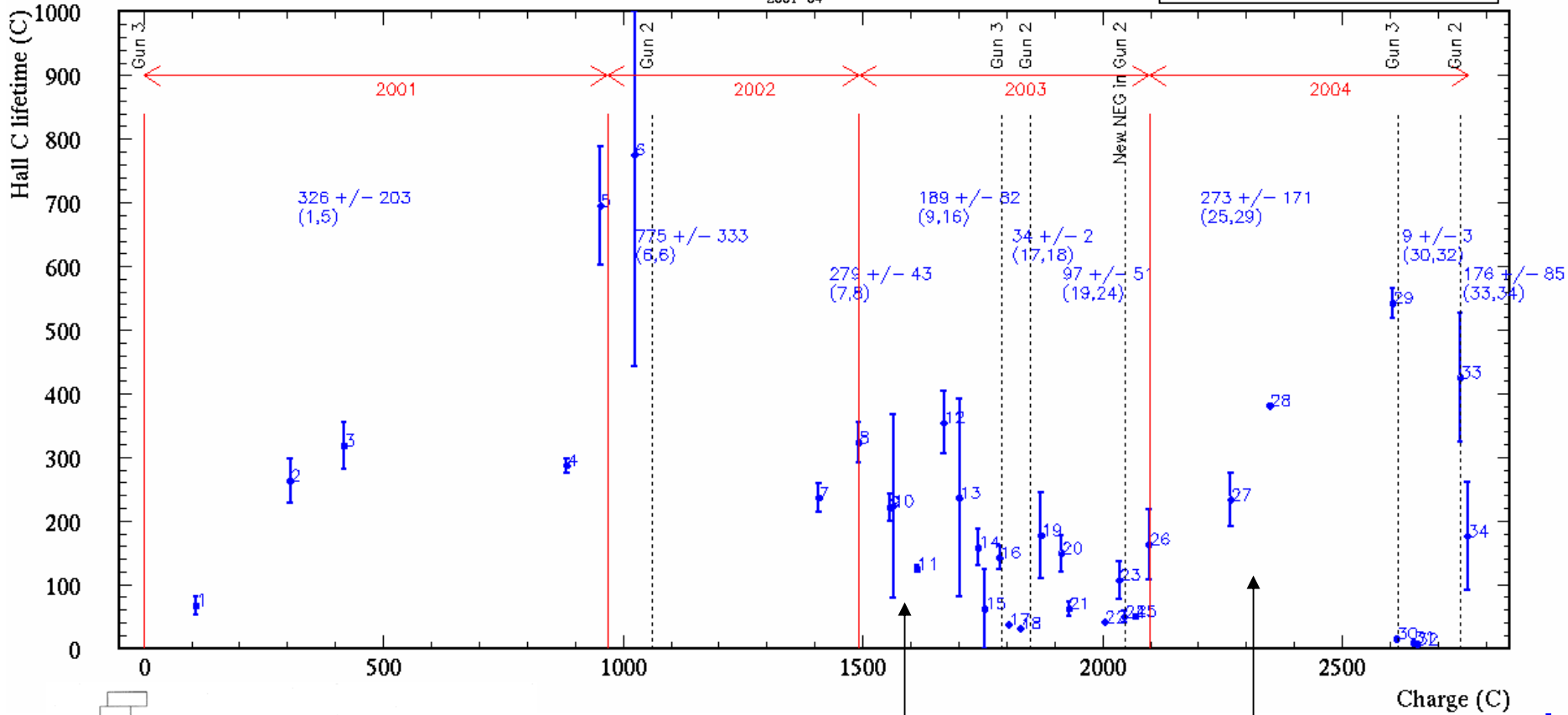
$$\text{Ultimate Pressure} = \frac{\text{Outgassing Rate} \times \text{Surface Area}}{\text{Pump Speed}}$$

We need: Smaller outgassing rate, Less surface area, More pump speed.



Gun Charge Lifetime Measured over 2001 -2004

Data compiled by M. Baylac



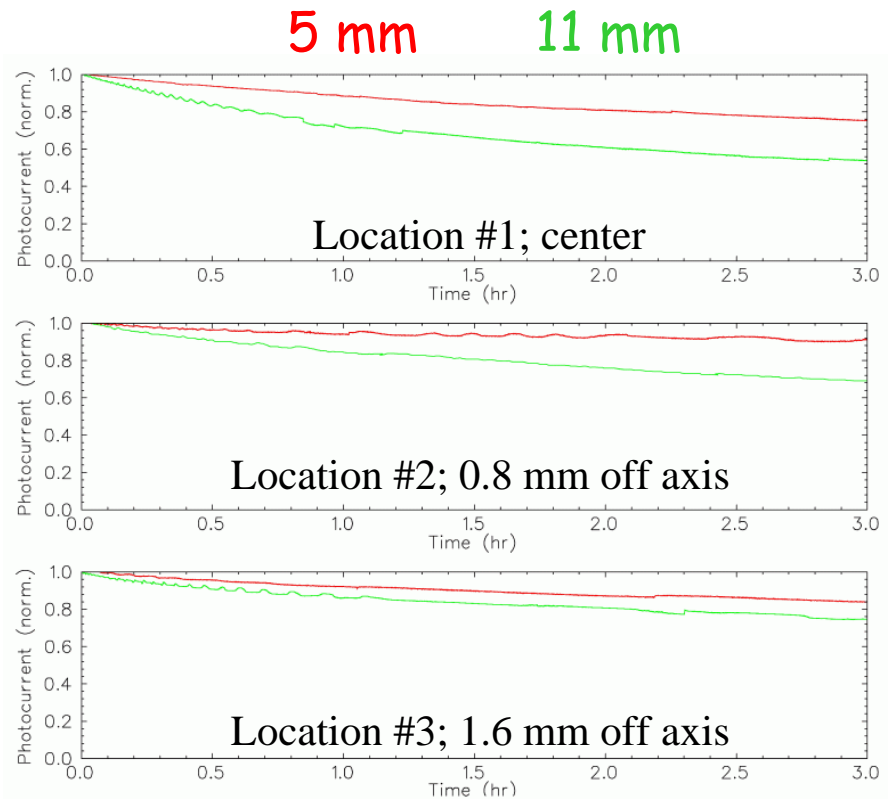
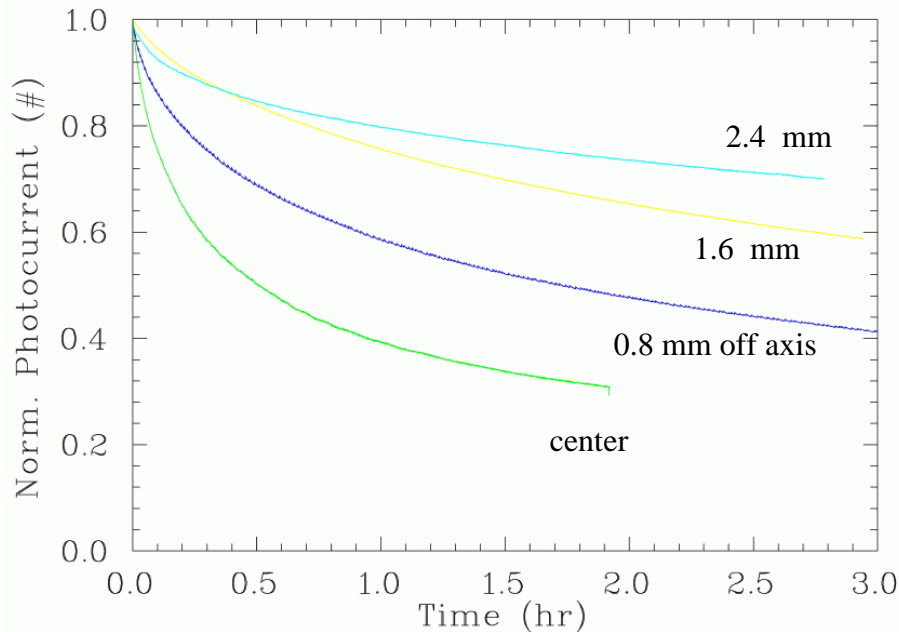
Gun Charge Lifetime Steadily Decreasing

NEG pump replacement Summer 2003 improves lifetime

Jefferson Lab

What Other Factors Effect Gun Lifetime?

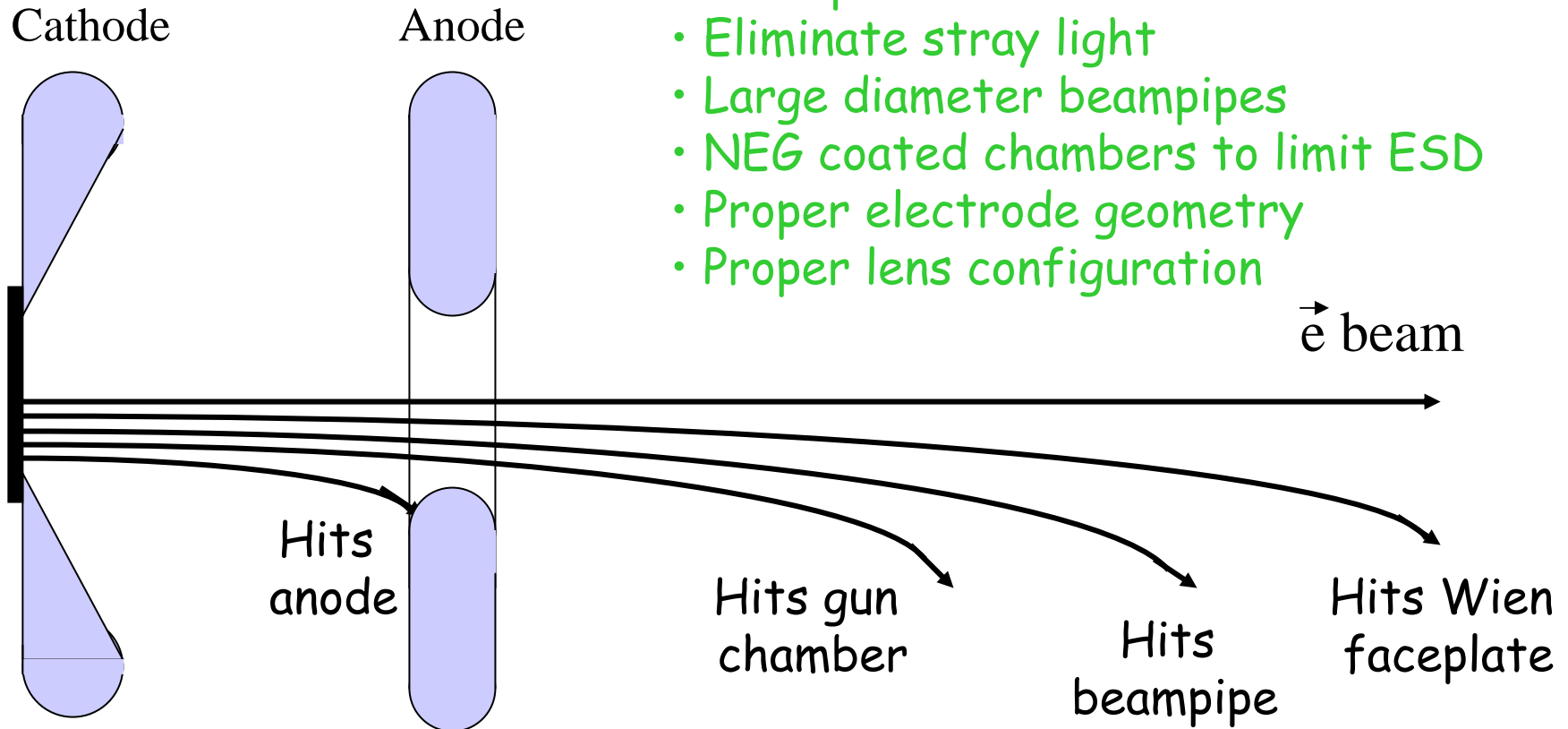
- Photocathode Active Area
- Radial position of laser spot on photocathode
- Laser wavelength ?
- Laser spot diameter ?



Managing the Extracted Electron Beam

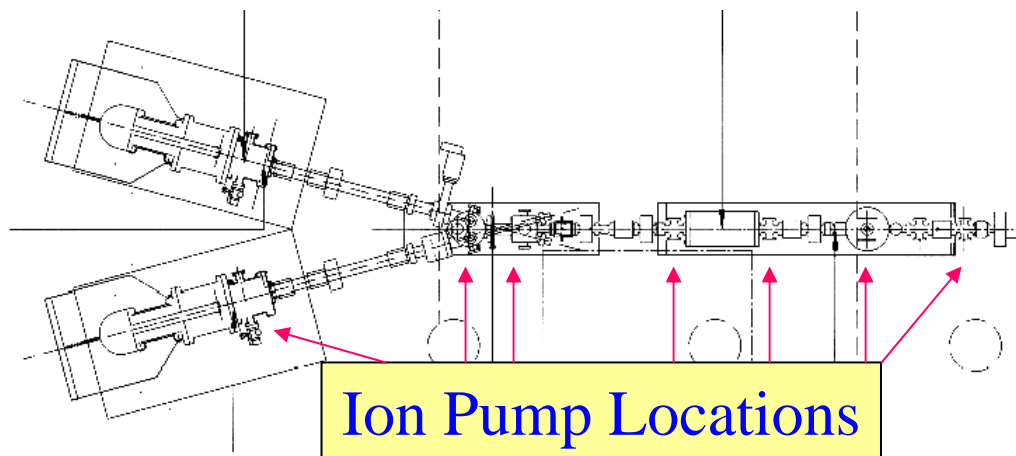
Why is this important? To preserve good vacuum and limit QE degradation associated with ion-backbombardment

- Limit photocathode active area
- Eliminate stray light
- Large diameter beampipes
- NEG coated chambers to limit ESD
- Proper electrode geometry
- Proper lens configuration



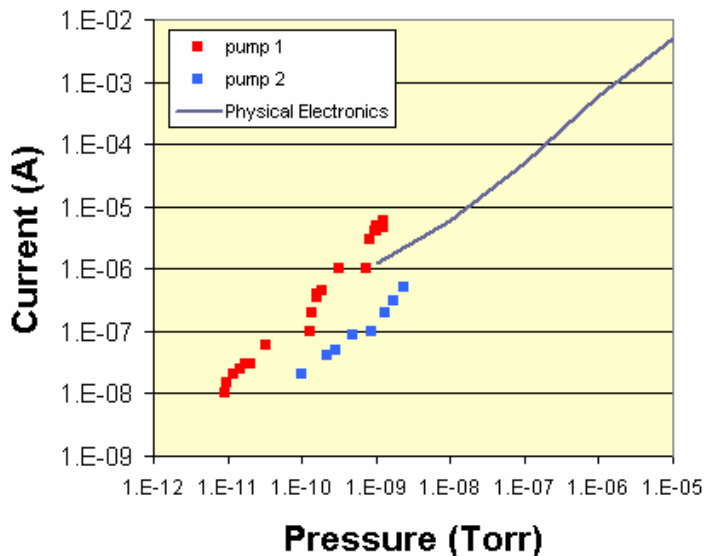
Ion Pump Power Supplies with nanoA Current Monitoring

Designed and constructed by J. Hansknecht

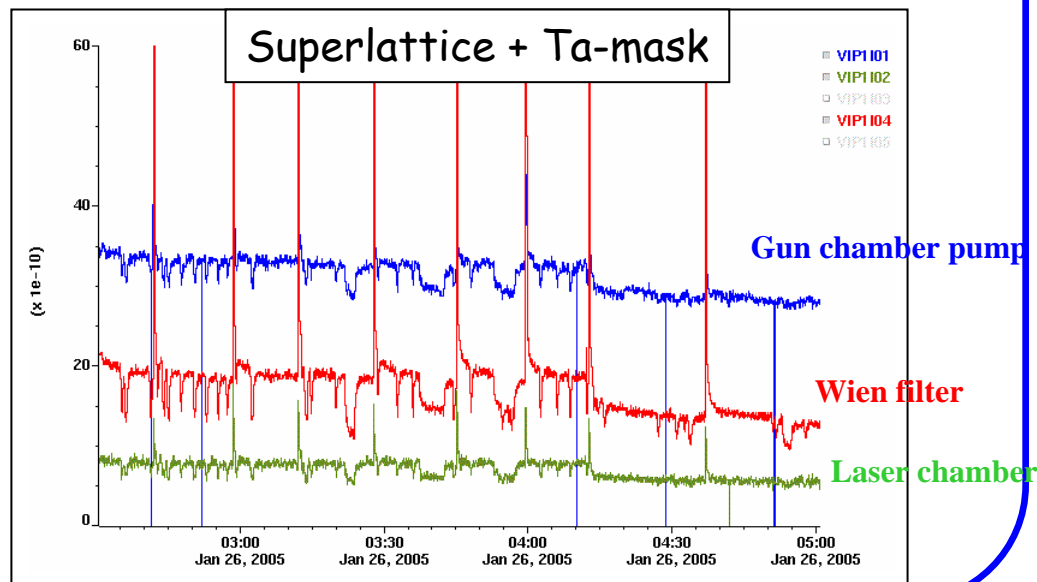


“Free” pressure monitoring at 10^{-11} Torr

UHV ion pump vs. extractor gauge



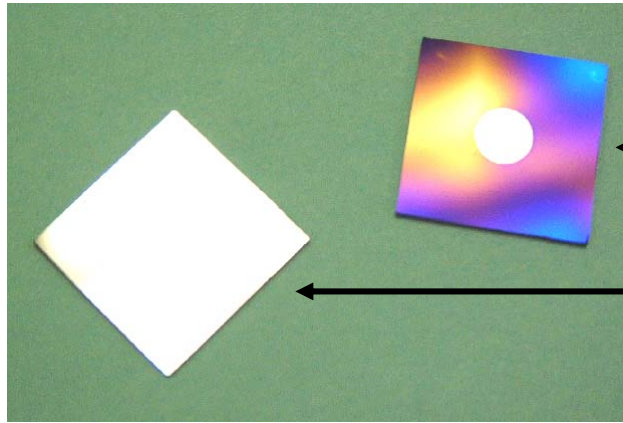
Pumps detect bad orbit and beamloss



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Limiting Active Area via Anodization

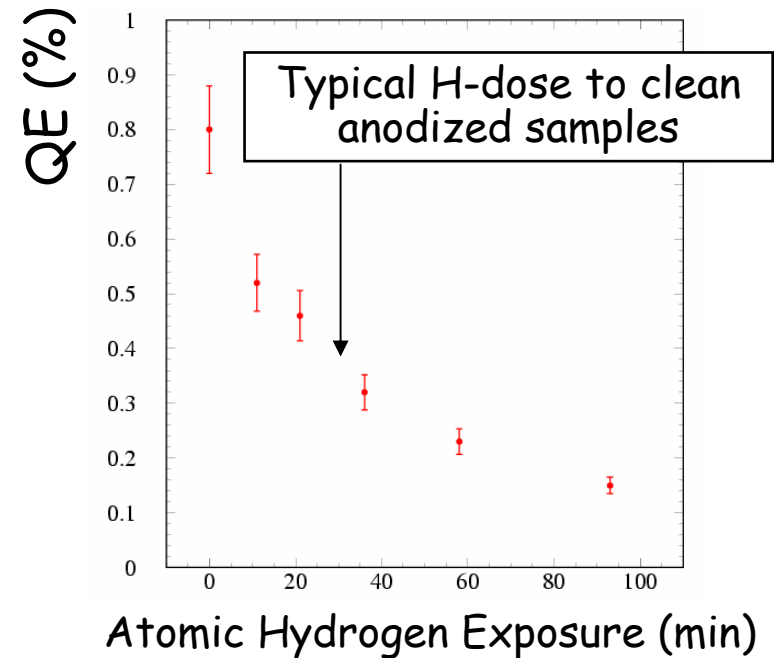


Anodized photocathode

Photocathode "out of box"

We have not successfully anodized superlattice material - it cannot be hydrogen cleaned.

We are using a tantalum mask, which might be the source of unwanted electrons.



"The Effects of Atomic Hydrogen Exposure On High Polarization GaAs Photocathodes", M. Baylac, in press.

, 2005



Summary

- Only superlattice photocathodes have demonstrated polarization $> 80\%$.
- Only superlattice photocathodes can (in principle) provide 1 mA with existing commercial modelocked Ti-Sapphire lasers.
- Superlattice photocathodes have good initial QE but lifetime at CEBAF has not been as good as for strained GaAs (problems with ta-mask?). QE falls with increasing laser power. More experience needed.
- TimeBandwidth sells reliable modelocked Ti-Sapphire lasers with rep rates to 500 MHz and ~ 500 mW power
- Laser development required for higher rep rates and higher power.



Summary cont.

- NEG pump speed drops rapidly at pressure below 10^{-11} Torr. Long lifetime operation at high current will require better vacuum: need better pumps, smaller chamber volume, smaller outgassing rate.
- Managing the extracted electron beam is critical (both "good" and "bad" beam). Groups working on new injectors will benefit from thoughtful modeling of beam that originates from the entire photocathode.
- Load locked guns are good. New CEBAF design to be installed Sept. 05. Duplicate at Test Cave will be very useful for high current/high polarization tests.
- It would be great to find a diode/amplifier alternative to Ti-Sapphire lasers. Superlattice photocathode support diode ops at 1.55 μm .



Gun Issues for ELIC

- Need 80% polarized e-beam.
- Use SVT superlattice photocathode. 1% QE at 780 nm;
 - 6.3 mA/W/%QE
 - ~ 1 W provides 1/e operation at 2.5 mA
- Commercial Ti-Sapp lasers with CW rep rates to 500 MHz provide 0.5 W. Homemade lasers provide ~ 2W.
- Injector micropulse/macropulse time structure demands laser R&D.
- 25 mA operation requires more laser power and/or QE.
- Charge Limit? Yes, at 1.6 nC/bunch and low QE wafers.
- Lifetime? Probably wise to improve vacuum (more later)
- Gun HV ~ 500 kV to mitigate emittance growth.
 - Must limit field emission.



Gun Lifetime

- CEBAF enjoys good gun lifetime;
 - ~ 200 C charge lifetime (until QE reaches $1/e$ of initial value)
 - ~ 100,000 C/cm² charge density lifetime (we operate with a ~ 0.5 mm dia. laser spot)
- Gun lifetime dominated by ion backbombardment.
- So it's reasonable to assume lifetime proportional to current density.
- Use a large laser spot to drive ELIC gun. This keeps charge density small. **Expect to enjoy the same charge density lifetime, despite higher ave. current operation, with existing vacuum technology.**



Gun Lifetime cont.

Lifetime Estimate;

- Use 1 cm diameter laser spot at photocathode.
- At 2.5 mA gun current, we deliver 9 C/hour, 216 C/week.
- Charge delivered until QE falls to 1/e of initial value;

$$100,000 \text{ C/cm}^2 * 1 \text{ Wk}/216 \text{ C} * 3.14(0.5 \text{ cm})^2 = 360 \text{ Wks!}$$

36 Weeks lifetime at 25 mA.

- Need to test the scalability of charge lifetime with laser spot diameter. Measure charge lifetime versus laser spot diameter in lab.



Laser Power and Max QE

- Present state of the art;
 - QE = 1% at ~ 80% polarization (SVT superlattice photocathode)
 - TimeBandwidth SESAM modelocked Ti-Sapphire laser with rep rates to 500 MHz and ave. power ~ 500 mW
 - "Homemade" modelocked Ti-Sapphire laser with rep rates to ~ 3 GHz and ave. power ~ 2 W (C. Hovater and M. Poelker, Nucl. Instr. And Meth. A418, 280 (1998)).
- We should be able to deliver 12.6 mA today! Albeit with a CW pulse structure.

